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ELECTRONICS

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Jameco Part Number 2057975

# MJ11028, MJ11030, MJ11032 (NPN) MJ11029, MJ11033 (PNP)

# High-Current Complementary Silicon Power Transistors

High-Current Complementary Silicon Power Transistors are for use as output devices in complementary general purpose amplifier applications.

# **Features**

- High DC Current Gain  $h_{FE} = 1000$  (Min) @  $I_C = 25$  Adc  $h_{FE} = 400$  (Min) @  $I_C = 50$  Adc
- Curves to 100 A (Pulsed)
- Diode Protection to Rated I<sub>C</sub>
- Monolithic Construction with Built-In Base-Emitter Shunt Resistor
- Junction Temperature to +200°C
- Pb-Free Packages are Available\*

# MAXIMUM RATINGS (T<sub>J</sub> = 25°C unless otherwise noted)

| Rating   |                                     | Symbol                            | Value           | Unit      |
|--|-------------------------------------|-----------------------------------|-----------------|-----------|
| Collector-Emitter Voltage  | MJ11028/29<br>MJ11030<br>MJ11032/33 | V <sub>CEO</sub>                  | 60<br>90<br>120 | Vdc       |
| Collector-Base Voltage   | MJ11028/29<br>MJ11030<br>MJ11032/33 | V <sub>CBO</sub>                  | 60<br>90<br>120 | Vdc       |
| Emitter-Base Voltage   |                                     | V <sub>EBO</sub>                  | 5.0             | Vdc       |
| Collector Current – Continuous<br>– Peak (Note 1)  |                                     | I <sub>C</sub>                    | 50<br>100       | Adc       |
| Base Current - Continuous  |                                     | Ι <sub>Β</sub>                    | 2.0             | Adc       |
| Total Power Dissipation @ T <sub>C</sub> = 25°C Derate Above 25°C @ T <sub>C</sub> = 100°C |                                     | P <sub>D</sub>                    | 300<br>1.71     | W<br>W/°C |
| Operating and Storage Junction<br>Temperature Range  |                                     | T <sub>J</sub> , T <sub>stg</sub> | -55 to +200     | °C        |

# THERMAL CHARACTERISTICS

| Characteristic   | Symbol         | Max  | Unit |
|--|----------------|------|------|
| Maximum Lead Temperature for Soldering Purposes for ≤ 10 seconds | TL             | 275  | °C   |
| Thermal Resistance, Junction-to-Case                             | $R_{	heta JC}$ | 0.58 | °C/W |

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

1. Pulse Test: Pulse Width = 5  $\mu$ s, Duty Cycle  $\leq$  10%.

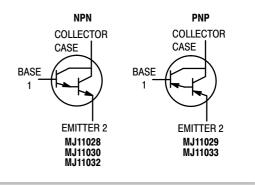
\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.



# ON Semiconductor®

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# 50 AMPERE COMPLEMENTARY DARLINGTON POWER TRANSISTORS 60 - 120 VOLTS 300 WATTS





TO-204 (TO-3) CASE 197A STYLE 1

# MARKING DIAGRAM



MJ110xx = Device Code

xx = 28, 29, 30, 32, 33

G = Pb-Free Package A = Location Code

YY = Year WW = Work Week MEX = Country of Orgin

# **ORDERING INFORMATION**

See detailed ordering and shipping information in the package dimensions section on page 3 of this data sheet.

# MJ11028, MJ11030, MJ11032 (NPN)

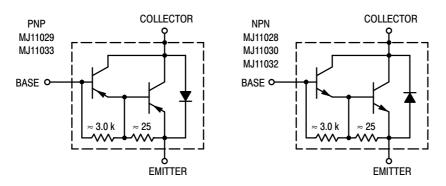


Figure 1. Darlington Circuit Schematic

# **ELECTRICAL CHARACTERISTICS** ( $T_C = 25^{\circ}C$ unless otherwise noted)

| Characteristic   |   | Symbol               | Min              | Max                     | Unit |
|--|---|----------------------|------------------|-------------------------|------|
| OFF CHARACTERISTICS  |   |                      | •                | •                       | •    |
| Collector-Emitter Breakdown Voltage (Note 1)<br>(I <sub>C</sub> = 1 00 mAdc, I <sub>B</sub> = 0)             | MJ11028, MJ11029<br>MJ11030<br>MJ11032, MJ11033   | V <sub>(BR)CEO</sub> | 60<br>90<br>120  | -<br>-<br>-             | Vdc  |
|  | MJ11028, MJ11029<br>MJ11030<br>MJ11032, MJ11033<br>MJ11028, MJ11029<br>MJ11032, MJ11033 | I <sub>CER</sub>     | -<br>-<br>-<br>- | 2<br>2<br>2<br>10<br>10 | mAdc |
| Emitter Cutoff Current (V <sub>BE</sub> = 5 Vdc, I <sub>C</sub> = 0)   |   | I <sub>EBO</sub>     | -                | 5                       | mAdc |
| Collector-Emitter Leakage Current (V <sub>CE</sub> = 50 Vdc, I <sub>B</sub> = 0)                             |   | I <sub>CEO</sub>     | _                | 2                       | mAdc |
| ON CHARACTERISTICS (Note 1)  |   |                      |                  |                         |      |
| DC Current Gain ( $I_C$ = 25 Adc, $V_{CE}$ = 5 Vdc) ( $I_C$ = 50 Adc, $V_{CE}$ = 5 Vdc)                      |   | h <sub>FE</sub>      | 1 k<br>400       | 18 k<br>-               | -    |
| Collector–Emitter Saturation Voltage ( $I_C$ = 25 Adc, $I_B$ = 250 mAdc) ( $I_C$ = 50 Adc, $I_B$ = 500 mAdc) |   | V <sub>CE(sat)</sub> | -<br>-           | 2.5<br>3.5              | Vdc  |
| Base-Emitter Saturation Voltage ( $I_C$ = 25 Adc, $I_B$ = 200 mAdc) ( $I_C$ = 50 Adc, $I_B$ = 300 mAdc)      |   | V <sub>BE(sat)</sub> | -<br>-           | 3.0<br>4.5              | Vdc  |

<sup>1.</sup> Pulse Test: Pulse Width  $\leq$  300  $\mu$ s, Duty Cycle  $\leq$  2.0%.

# MJ11028, MJ11030, MJ11032 (NPN)

## **ORDERING INFORMATION**

| Device   | Package             | Shipping         |
|----------|---------------------|------------------|
| MJ11028  | TO-204              |                  |
| MJ11028G | TO-204<br>(Pb-Free) |                  |
| MJ11029  | TO-204              |                  |
| MJ11029G | TO-204<br>(Pb-Free) |                  |
| MJ11030  | TO-204              |                  |
| MJ11030G | TO-204<br>(Pb-Free) | 100 Units / Tray |
| MJ11032  | TO-204              |                  |
| MJ11032G | TO-204<br>(Pb-Free) |                  |
| MJ11033  | TO-204              |                  |
| MJ11033G | TO-204<br>(Pb-Free) |                  |

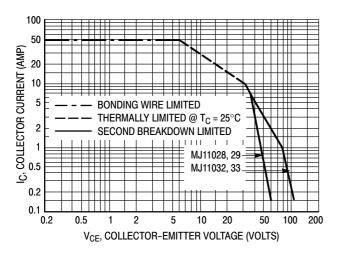


Figure 2. DC Safe Operating Area

There are two limitations on the power–handling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate  $I_C$  –  $V_{CE}$  limits of the transistor that must be observed for reliable operation, i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Figure 2 is based on  $T_{J(pk)} = 200^{\circ}C$ ;  $T_C$  is variable depending on conditions. At high case temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by second breakdown.

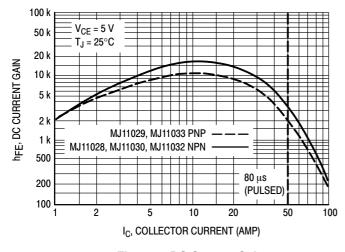


Figure 3. DC Current Gain

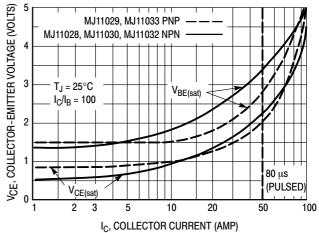
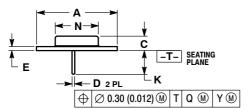


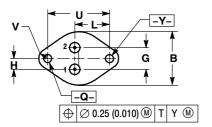
Figure 4. "On" Voltage

# MJ11028, MJ11030, MJ11032 (NPN)

# PACKAGE DIMENSIONS

**TO-204 (TO-3)** CASE 197A-05 ISSUE K





### NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M. 1982.
- 2. CONTROLLING DIMENSION: INCH.

|     | INCHES          |       | MILLIMETERS |       |
|-----|-----------------|-------|-------------|-------|
| DIM | MIN             | MAX   | MIN         | MAX   |
| Α   | 1.530 REF       |       | 38.86 REF   |       |
| В   | 0.990           | 1.050 | 25.15       | 26.67 |
| С   | 0.250           | 0.335 | 6.35        | 8.51  |
| D   | 0.057           | 0.063 | 1.45        | 1.60  |
| E   | 0.060           | 0.070 | 1.53        | 1.77  |
| G   | 0.430 BSC       |       | 10.92 BSC   |       |
| Н   | 0.215 BSC       |       | 5.46 BSC    |       |
| K   | 0.440           | 0.480 | 11.18       | 12.19 |
| L   | 0.665 BSC 16.89 |       | BSC         |       |
| N   | 0.760           | 0.830 | 19.31       | 21.08 |
| Q   | 0.151           | 0.165 | 3.84        | 4.19  |
| U   | 1.187 BSC       |       | 30.15 BSC   |       |
| ٧   | 0.131           | 0.188 | 3.33        | 4.77  |

STYLE 1: PIN 1. BASE 2. EMITTER CASE: COLLECTOR

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